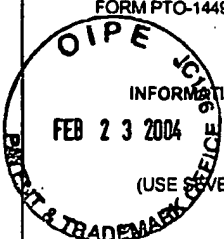


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	APPLICANT Hannu Huotari	
	FILING DATE June 19, 2003	GROUP ART UNIT 2811

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
CK	1. Chatterjee et al., "CMOS Metal Replacement Gate Transistors using Tantalum Pentoxide Gate Insulator," IEEE, IEDM, 0-7803-4774-9/98, pp. 777-780 (1998)
CK	2. Chen et al., "0.18 μ m Metal Gate Fully-Depleted SOI MOSFETs for Advanced CMOS Applications," Symposium on VLSI Technology Digest of Technical Papers, pp. 25-26 (1999)
CK	3. Ducroquet et al., "Full CMP Integration of CVD TiN Damascene Sub-0.1- μ m Metal Gate Devices For ULSI Applications," IEEE Transactions on Electron Devices, Vol 48, No. 8, pp. 1816-1821 (2001)
CK	4. Ferguson et al., "Titanium Nitride Metal Gate Electrode: Effect of Nitrogen Incorporation," Advanced Metallization Conference 2001 (AMC 2001), pp. 115-119
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CK	7. Park et al., "Robust Ternary Metal Gate Electrodes for Dual Gate CMOS Devices," IEEE, IEDM, 0-7803-7050-3/02, pp. 671-674 (2001)
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CK	9. Wakabayashi et al., "A Novel W/TiNx Metal Gate CMOS Technology using Nitrogen-Concentration-Controlling TiNx Film," IEEE, IEDM, 0-7803-5410-9/99, pp. 253-256 (1999)
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